PDTD123E series

NPN 500 mA, 50 V resistor-equipped transistors;R1 = 2.2 k Ω , R2 = 2.2 k Ω Rev. 02 — 16 November 2009Pro

Product data sheet

1. Product profile

1.1 General description

500 mA NPN Resistor-Equipped Transistors (RET) family.

Table 1. Product overview

Type number	Package		PNP complement	
	NXP	JEITA	JEDEC	
PDTD123EK	SOT346	SC-59A	TO-236	PDTB123EK
PDTD123ES ^[1]	SOT54	SC-43A	TO-92	PDTB123ES
PDTD123ET	SOT23	-	TO-236AB	PDTB123ET

[1] Also available in SOT54A and SOT54 variant packages (see Section 2).

1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- 500 mA output current capability

1.3 Applications

- Digital application in automotive and industrial segments
- Controlling IC inputs

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
I _O	output current (DC)		-	-	500	mA
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		0.9	1.0	1.1	



- Reduces component count
- Reduces pick and place costs
- ±10 % resistor ratio tolerance
- Cost saving alternative for BC817 series in digital applications
- Switching loads

2. Pinning information

Pin	Description	Simplified outline	Symbol
SOT54			
1	input (base)		
2	output (collector)		2
3	GND (emitter)	001aab347	1 R2 006aaa145
SOT54A			
1	input (base)		
2	output (collector)		2
3	GND (emitter)	1 2 001aab348	1 R1 R2 3 006aaa145
SOT54 va	riant		
1	input (base)		
2	output (collector)	T =	R1 2
3	GND (emitter)	001aab447	1 R2 006aaa145
SOT23, S	OT346		
1	input (base)		
2	GND (emitter)	3	3
3	output (collector)	12	1 R1 R2 sym007

3. Ordering information

Type number	Package		
	Name	Description	Version
PDTD123EK	SC-59A	plastic surface mounted package; 3 leads	SOT346
PDTD123ES ^[1]	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54
PDTD123ET	-	plastic surface mounted package; 3 leads	SOT23

[1] Also available in SOT54A and SOT54 variant packages (see Section 2 and Section 9).

4. Marking

Table 5.Marking codes

Type number	Marking code ^[1]
PDTD123EK	E3
PDTD123ES	D123ES
PDTD123ET	*7T

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

5. Limiting values

Table 6.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter	-	50	V
V _{CEO}	collector-emitter voltage	open base	-	50	V
V _{EBO}	emitter-base voltage	open collector	-	10	V
VI	input voltage				
	positive		-	+12	V
	negative		-	-10	V
lo	output current (DC)		-	500	mA
P _{tot}	total power dissipation	$T_{amb} \leq 25 ~^{\circ}C$	<u>[1]</u>		
	SOT346		-	250	mW
	SOT54		-	500	mW
	SOT23		-	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 7.	Thermal characteristics	5				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u>			
	SOT346		-	-	500	K/W
	SOT54		-	-	250	K/W
	SOT23		-	-	500	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

7. Characteristics

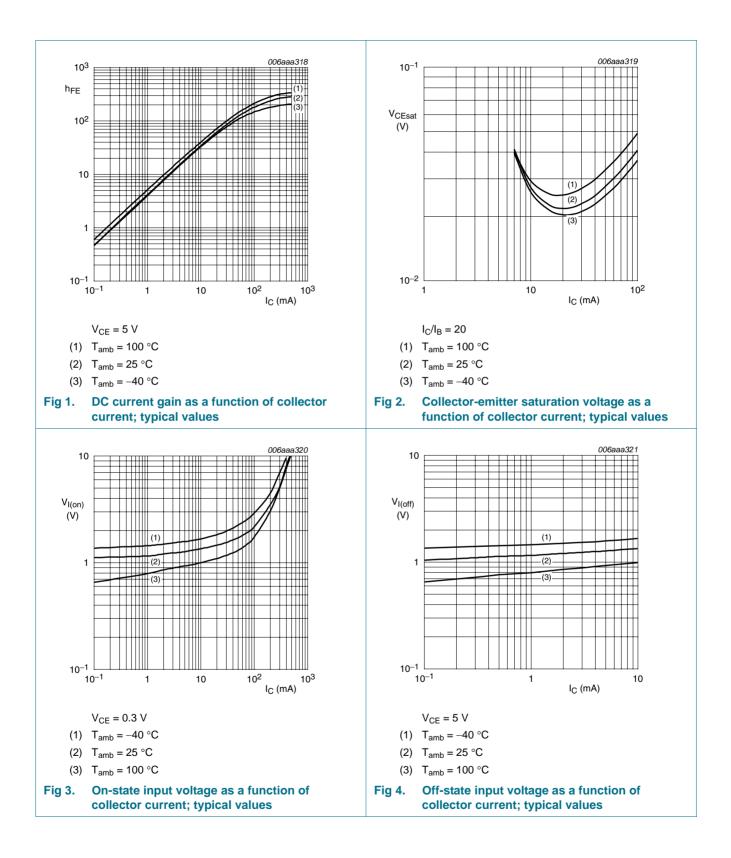
Table 8. $T_{amb} = 25$	Characteristics ℃ unless otherwise sp	pecified.				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	$V_{CB} = 40 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
(current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = 50 \text{ V}; I_B = 0 \text{ A}$	-	-	0.5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 V; I_{C} = 0 A$	-	-	2	mA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 50 \text{ mA}$	40	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_{\rm C}$ = 50 mA; $I_{\rm B}$ = 2.5 mA	-	-	0.3	V
V _{I(off)}	off-state input voltage	$V_{CE} = 5 \text{ V}; \text{ I}_{C} = 100 \mu\text{A}$	0.6	1.1	1.8	V
V _{I(on)}	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 20 \text{ mA}$	1.0	1.5	2.0	V
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		0.9	1.0	1.1	
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 100 MHz	-	7	-	pF

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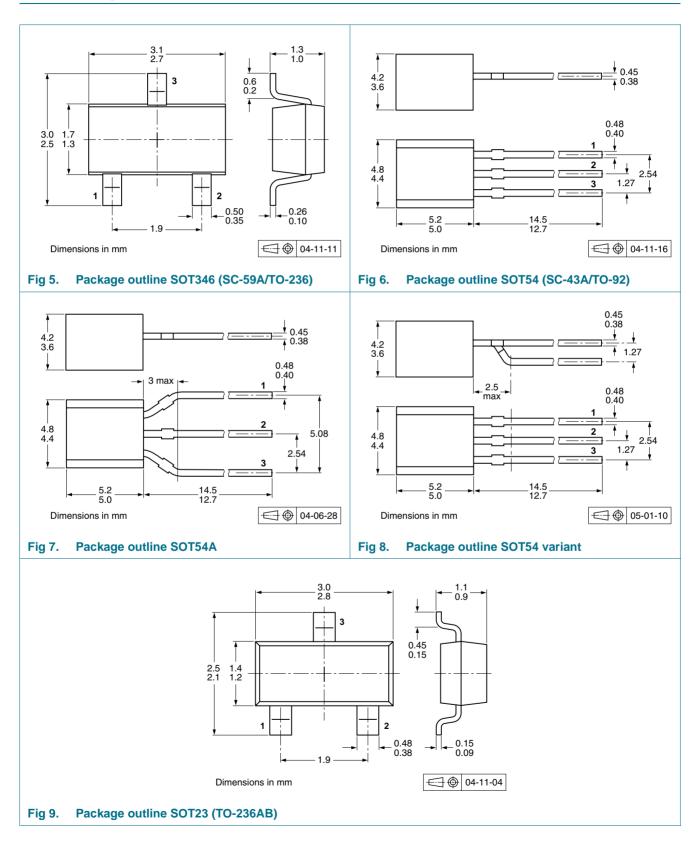
Product data sheet

PDTD123E series

NPN 500 mA resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω



8. Package outline



9. Packing information

Type number	Package	Description	Packin	g quantit	y
			3000	5000	10000
PDTD123EK	SOT346	4 mm pitch, 8 mm tape and reel	-115	-	-135
PDTD123ES	SOT54	bulk, straight leads	-	-412	-
	SOT54A	tape and reel, wide pitch	-	-	-116
		tape ammopack, wide pitch	-	-	-126
	SOT54 variant	bulk, delta pinning	-	-112	-
PDTD123ET	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235

[1] For further information and the availability of packing methods, see <u>Section 12</u>.

10. Revision history

Table 10. Revision h	istory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTD123E_SER_2	20091116	Product data sheet	-	PDTD123E_SER_1
Modifications:		eet was changed to reflect w legal definitions and disc		
PDTD123E_SER_1	20050408	Product data sheet	-	-

11. Legal information

11.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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PDTD123E series

NPN 500 mA resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

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